

20A Low Barrier Diode

■ Features

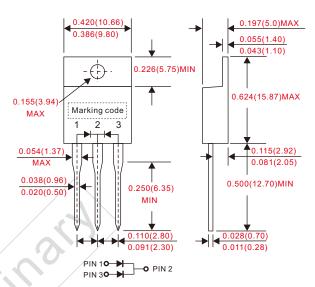
- · Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CS20S100CTG-A.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

■ Mechanical data

- Epoxy: UL94-V0 rated flame retardant.
- Case: JEDEC TO-220AB molded plastic body over passivated chip.
- Lead : Axial leads, solderable per MIL-STD-202, Method 208 guranteed.
- Polarity: Color band denotes cathode end.
- Mounting Position : Any.
- Weight: Approximated 2.25 gram.

Outline

TO-220AB



Dimensions in inches and (millimeters)

■ Maximum ratings and electrical characteristics

Rating at 25° C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CS20S100CT-A	UNIT
Marking code			CS20S100CT	
Peak repetitive reverse voltage		V _{RRM}		
Working peak reverse voltage		V _{RWM}	100	V
DC blocking voltage		V _{RM}		
Forward rectified current (total device)		Io	20	Α
Forward surge current (per diode)	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}	200	А
Peak repetitive reverse surge current (per diode)	2us - 1kHz	I _{RRM}	3	А
Thermal resistance(1) (per diode)	Junction to case	R _{eJC}	2	°C/W
Operating and Storage temperature		T _J , T _{STG}	-65 ~ +175	°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage drop (per diode)	$I_F = 10A, T_J = 25^{\circ}C$	V _F			700	mV
	$I_F = 10A, T_J = 125^{\circ}C$			570	630	
	$I_F = 20A, T_J = 25^{\circ}C$				820	
I Reverse current (ner diode)	$V_R = V_{RRM} T_J = 25^{\circ}C$	- I _R			0.5	mA
	$V_R = V_{RRM} T_J = 125^{\circ}C$				25	

Note: 1.Thermal resistance from junction to case per leg, with heatsink size(1.35" x 0.95" x 0.18") Al-plate.

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■ Rating and characteristic curves

Fig. 1 - Forward Power Dissipation (per diode)

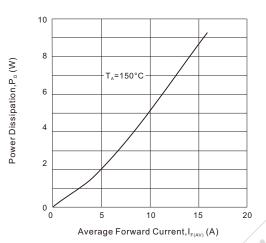


Fig. 2 - Instantaneous Forward Characteristics (per diode)

100

T_A=150°C

T_A=150°C

T_A=75°C

0.1

0.1

0.1

0.2

0.3

0.4

0.5

0.6

0.7

0.8

0.9

Instantaneous Forward Voltage, V_F (Volts)

Fig. 3 - Reverse Characteristics (per diode)

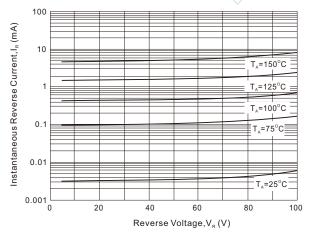
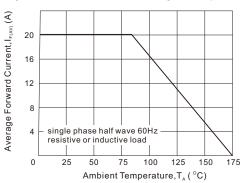


Fig.4 - Forward Current Derating Curve (total device)



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